IN THE CLAIMS

Please cancel claims 3, 4, and 6 without prejudice.

Please amend the following claims which are pending in the present application:

1. (Currently amended) A method of fabricating a microelectronic die, comprising:

manufacturing transistors in and on a semiconductor substrate; [[and]]

~~stressing~~ forming an intermediate substrate on a handle substrate;

allowing the intermediate substrate and handle substrate to cool, the intermediate substrate having a different CTE than the handle substrate;

connecting the semiconductor substrate to the intermediate substrate; and

at least partially removing the handle substrate to stress a channel of each transistor after the transistors are manufactured.

2. (Original) The method of claim 1, wherein a tensile stress is applied to each channel.

3-4. (Cancelled)

5. (Currently amended) The method of claim [[4]] 1, wherein the intermediate substrate is made of diamond.

6. (Cancelled)

7. (Currently amended) The method of claim [[6]] 1, wherein the intermediate substrate and the handle substrate bow into a first shape when allowed to cool, and the semiconductor substrate and the intermediate substrate bow into a final shape when the handle substrate is removed.

8. (Original) The method of claim 7, further comprising:

changing the first shape into a second shape with less bow than the first shape before the semiconductor substrate is connected to the intermediate substrate.

9. (Original) The method of claim 8, wherein the first shape is changed into the second shape by applying a compensating layer.

10. (Original) The method of claim 9, wherein the compensating layer is made of silicon.

11. (Original) The method of claim 9, wherein the compensating layer is formed on major surfaces of both the intermediate substrate and the handle substrate but has a different CTE on the intermediate substrate than on the handle

substrate.

12. (Original) The method of claim 1, further comprising:

singulating the semiconductor substrate after the channels are stressed.

13. (Currently amended) A method of fabricating a microelectronic die, comprising:

forming a first combination wafer, including a handle substrate and an intermediate substrate on the handle substrate;

allowing the first combination wafer to cool, the intermediate substrate having a lower CTE than the handle substrate so that the combination wafer bows into a first shape;

forming a compensating layer on the combination wafer to form a second combination wafer[[,]] ;

allowing the second combination wafer to cool, the compensating layer having a CTE which, compared to the CTEs of the handle substrate and the intermediate substrate, changes the first shape into a second shape with less bow;

connecting a semiconductor substrate to the second combination wafer; and

at least partially removing the handle substrate to change the second shape into a third shape and create a stress in the semiconductor substrate.

14. (Original) The method of claim 13, further comprising:

forming a plurality of transistors in and on the semiconductor substrate before removing the handle substrate.

15. (Original) The method of claim 13, wherein the intermediate substrate is made of diamond.

16. (Original) The method of claim 13, wherein the compensating layer is made of silicon.

17. (Original) The method of claim 13, wherein the compensating layer is formed on major surfaces of both the intermediate substrate and the handle substrate but has a different CTE on the intermediate substrate than on the handle substrate.

18-21. (Cancelled)